

Features

- Trench LV MOSFET Technology
- High Density Cell Design for Ultra Low $R_{DS(on)}$
- Moisture Sensitivity Level 1
- Halogen Free. "Green" Device (Note 1)
- Epoxy Meets UL 94 V-0 Flammability Rating
- Lead Free Finish/RoHS Compliant ("P" Suffix Designates RoHS Compliant. See Ordering Information)

Maximum Ratings

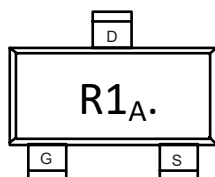
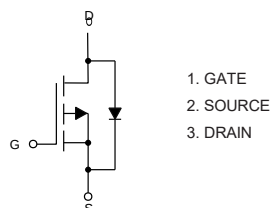
- Operating Junction Temperature Range : -55°C to +150°C
- Storage Temperature Range: -55°C to +150°C
- Thermal Resistance: 104°C/W Junction to Ambient (Note2)

Parameter	Symbol	Rating	Unit
Drain-Source Voltage	V_{DS}	-30	V
Gate-Source Voltage	V_{GS}	±12	V
Continuous Drain Current	$T_A=25^\circ\text{C}$	I_D	A
	$T_A=100^\circ\text{C}$		
Pulsed Drain Current (Note3)	I_{DM}	-16.8	A
Total Power Dissipation (Note4)	P_D	1.2	W

Note:

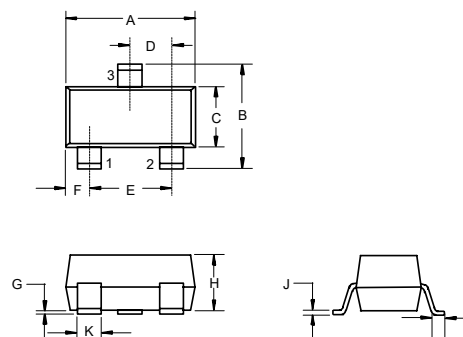
1. Halogen free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
2. The value of $R_{\theta JA}$ is measured with the device mounted on 1in² FR-4 board with 2oz. Copper, in a still air environment with $T_A=25^\circ\text{C}$.
3. Repetitive rating; pulse width limited by max. junction temperature.
4. P_D is based on max. junction temperature, using junction-ambient thermal resistance.

Internal Structure and Marking Code



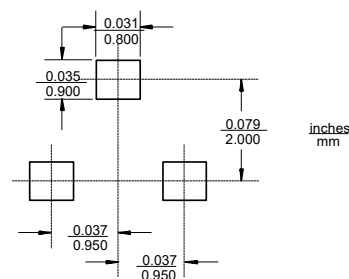
P-CHANNEL MOSFET

SOT-23



DIMENSIONS					
DIM	INCHES		MM		NOTE
	MIN	MAX	MIN	MAX	
A	0.110	0.120	2.80	3.04	
B	0.083	0.104	2.10	2.64	
C	0.047	0.055	1.20	1.40	
D	0.034	0.041	0.85	1.05	
E	0.067	0.083	1.70	2.10	
F	0.018	0.024	0.45	0.60	
G	0.0004	0.006	0.01	0.15	
H	0.035	0.043	0.90	1.10	
J	0.003	0.007	0.08	0.18	
K	0.012	0.020	0.30	0.51	
L	0.007	0.020	0.20	0.50	

Suggested Solder Pad Layout



ELECTRICAL CHARACTERISTICS (Ta=25°C unless otherwise specified)

Parameter	Symbol	Test conditions	Min	Typ	Max	Unit
Static Characteristics						
Drain-Source Breakdown Voltage	V _{(BR)DSS}	V _{GS} =0V, I _D =-250μA	-30			V
Gate-Threshold Voltage	V _{GS(th)}	V _{DS} =V _{GS} , I _D =-250μA	-0.7	-0.85	-1.3	V
Gate-Body Leakage Current	I _{GSS}	V _{GS} =±12V, V _{DS} =0V			±100	nA
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} =-24V, V _{GS} =0V			-1	μA
Drain-Source On-Resistance	R _{DS(on)}	V _{GS} =-10V, I _D =-4.2A		45	60	mΩ
		V _{GS} =-4.5V, I _D =-4A		52	70	
		V _{GS} =-2.5V, I _D =-1A		68	85	
Forward Transconductance	g _{FS}	V _{DS} =-5V, I _D =-4.5A		14		S
Gate Resistance	R _g	f=1 MHz, Open drain		9		Ω
Diode Characteristics						
Continuous Body Diode Current	I _S				-4.2	A
Diode Forward Voltage	V _{SD}	V _{GS} =0V, I _S =-1A			-1	V
Reverse Recovery Time	t _{rr}	I _F =-2A, dI _F /dt=100A/μs		12		ns
Reverse Recovery Charge	Q _{rr}			4		nC
Dynamic Characteristics						
Input Capacitance	C _{iss}	V _{DS} =-15V,V _{GS} =0V,f=1MHz		831		pF
Output Capacitance	C _{oss}			68		
Reverse Transfer Capacitance	C _{rss}			59		
Total Gate Charge	Q _g	V _{DS} =-15V,V _{GS} =-10V,I _D =-2A		16.5		nC
Gate-Source Charge	Q _{gs}			1.3		
Gate-Drain Charge	Q _{gd}			2		
Turn-On Delay Time	t _{d(on)}	V _{DD} =-15V,V _{GS} =-10V, R _G =10Ω, I _D =-2A		5		ns
Turn-On Rise Time	t _r			3		
Turn-Off Delay Time	t _{d(off)}			40		
Turn-Off Fall Time	t _f			14		

Curve Characteristics

Fig.1 - Typical Output Characteristics

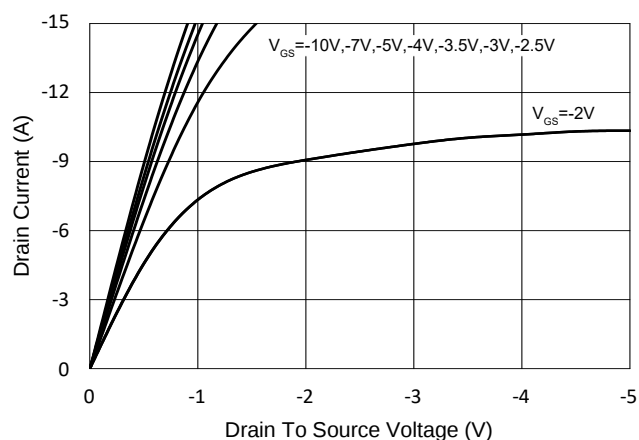


Fig.2 - Transfer Characteristic

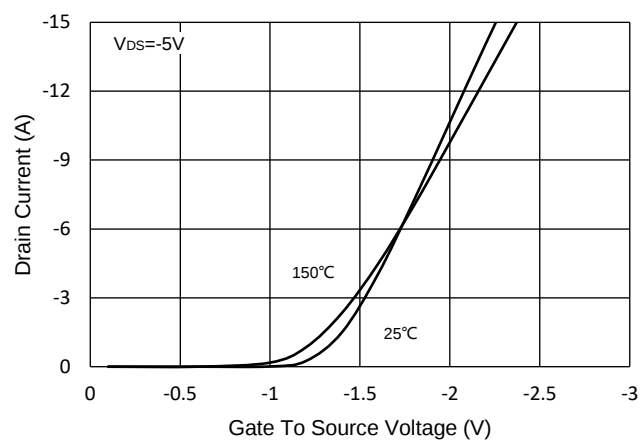


Fig.3 - $R_{DS(ON)}$ - V_{GS}

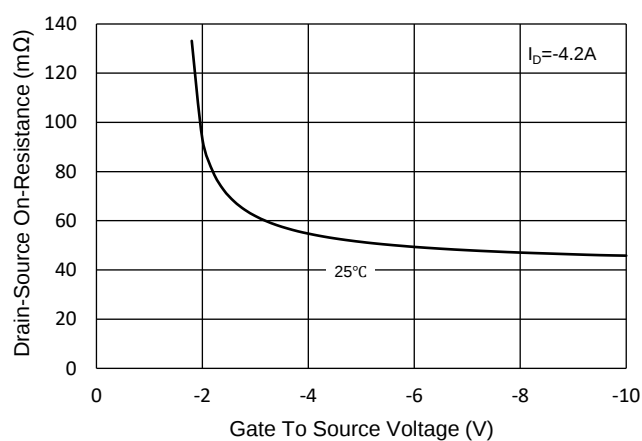


Fig.4 - $R_{DS(ON)}$ - I_D

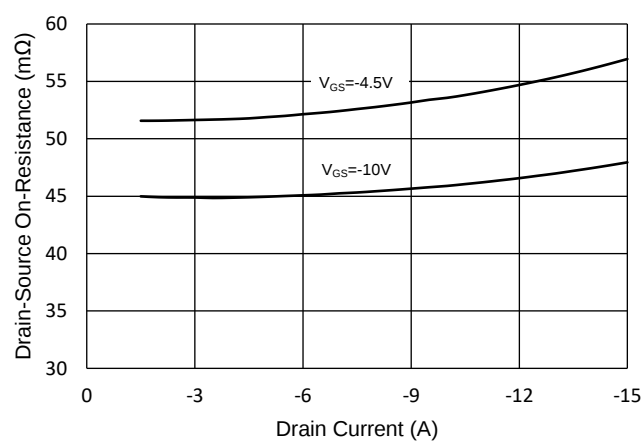


Fig.5 - Capacitance Characteristics

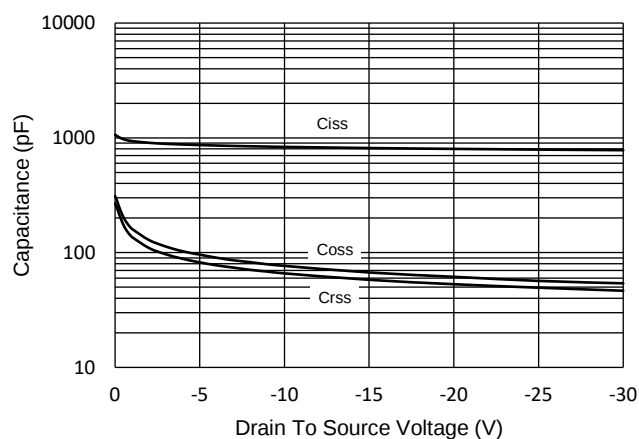
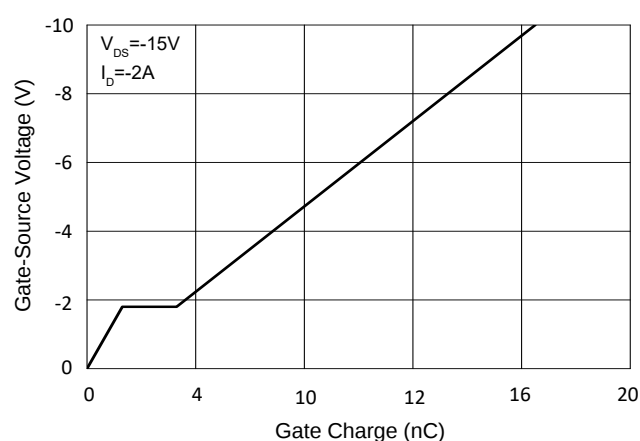


Fig.6 - Gate Charge



Curve Characteristics

Fig.7 - Normalized Threshold Voltage

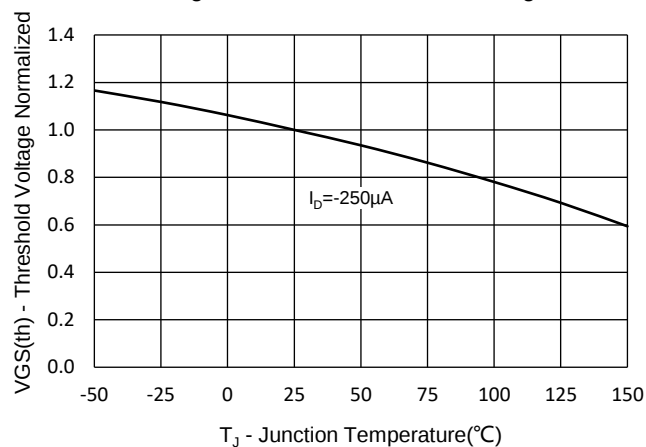


Fig.8 - Normalized On Resistance Characteristics

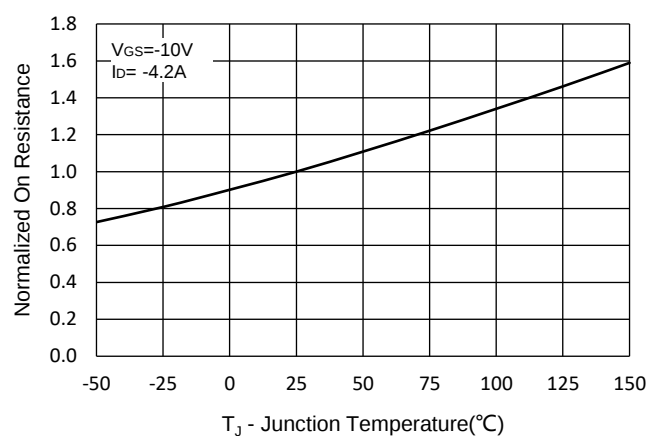


Fig.9 - I_S - V_{SD}

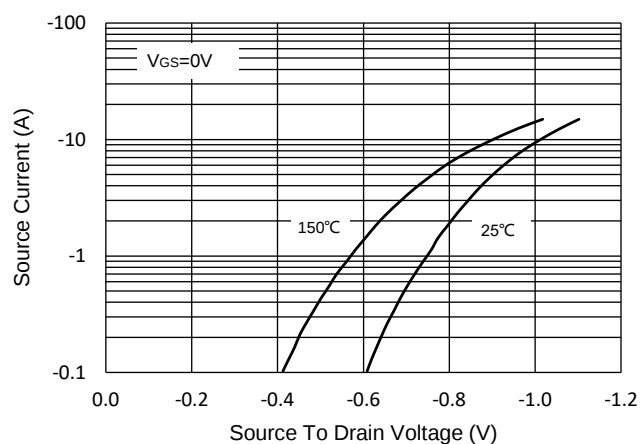


Fig.10 - Drain Current

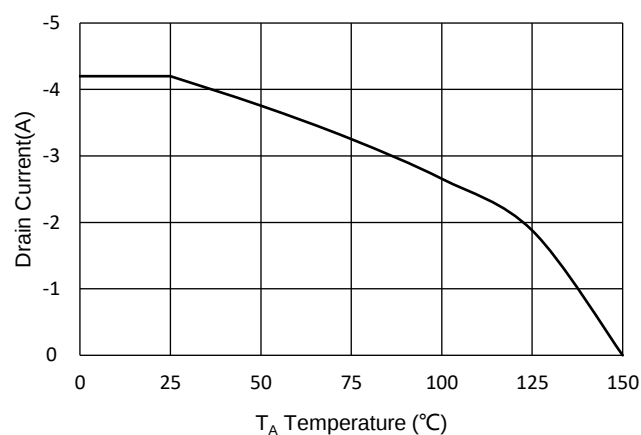
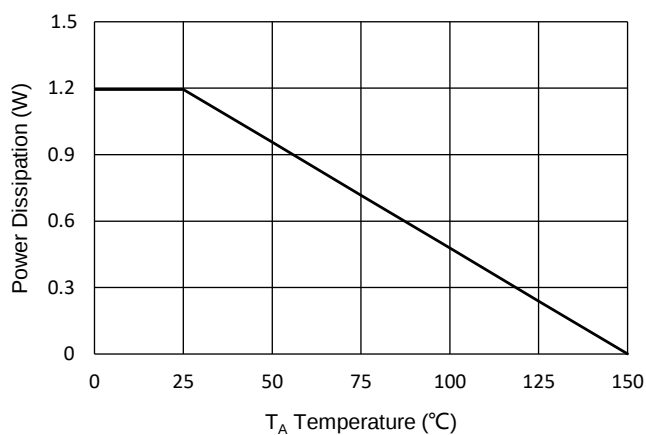


Fig.11 - PD Dissipation



Curve Characteristics

Fig.12 - Safe Operation Area

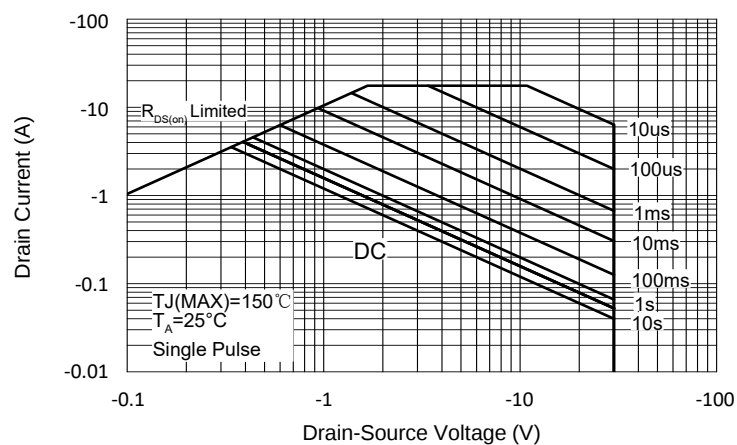
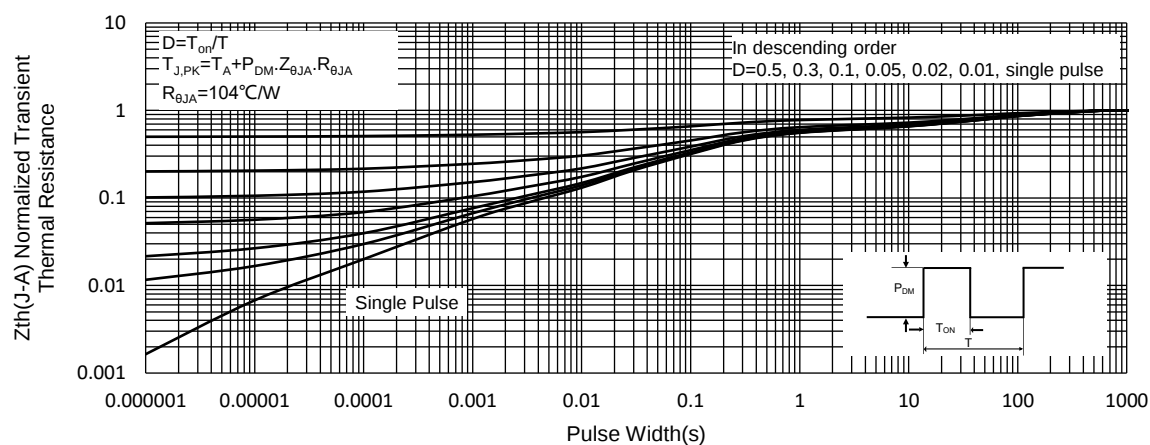


Fig.13 - Normalized Transient Thermal Impedance



Ordering Information

Device	Packing
Part Number-TP	Tape&Reel: 3Kpcs/Reel
Part Number-13P	Tape&Reel: 10Kpcs/Reel

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